ON Semiconductor

Is Now



To learn more about onsemi[™], please visit our website at www.onsemi.com

onsemi and ONSEMI. and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/ or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application,

One Watt High Current Transistors

PNP Silicon

Features

• These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage MPSW51 MPSW51A	V _{CEO}	-30 -40	Vdc
Collector - Base Voltage MPSW51 MPSW51A	V _{CBO}	-40 -50	Vdc
Emitter - Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current - Continuous	I _C	-1000	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	1.0 8.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	2.5 20	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

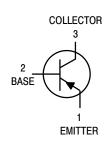
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	50	°C/W

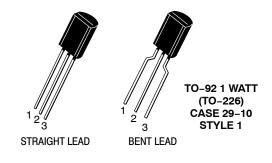
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



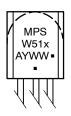
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAM



x = 51A Devices

A = Assembly Location

Y = Year

WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

$\textbf{ELECTRICAL CHARACTERISTICS} \ (T_A = 25^{\circ}\text{C unless otherwise noted})$

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS				•	
Collector – Emitter Breakdown Voltage (Note 1) $(I_C = -1.0 \text{ mAdc}, I_B = 0)$	MPSW51 MPSW51A	V _{(BR)CEO}	-30 -40	- -	Vdc
Collector – Base Breakdown Voltage (I _C = –100 μAdc, I _E = 0)	MPSW51 MPSW51A	V _{(BR)CBO}	-40 -50	- -	Vdc
Emitter – Base Breakdown Voltage (I _E = -100 µAdc, I _C = 0)		V _{(BR)EBO}	-5.0	_	Vdc
Collector Cutoff Current $(V_{CB} = -30 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -40 \text{ Vdc}, I_E = 0)$	MPSW51 MPSW51A	I _{CBO}	- -	-0.1 -0.1	μAdc
Emitter Cutoff Current (V _{EB} = -3.0 Vdc, I _C = 0)		I _{EBO}	-	-0.1	μAdc
ON CHARACTERISTICS	<u>.</u>				
DC Current Gain $ \begin{array}{l} (I_C = -10 \text{ mAdc, V}_{CE} = -1.0 \text{ Vdc}) \\ (I_C = -100 \text{ mAdc, V}_{CE} = -1.0 \text{ Vdc}) \\ (I_C = -1000 \text{ mAdc, V}_{CE} = -1.0 \text{ Vdc}) \end{array} $		h _{FE}	55 60 50	- - -	-
Collector – Emitter Saturation Voltage ($I_C = -1000 \text{ mAdc}$, $I_B = -100 \text{ mAdc}$)		V _{CE(sat)}	_	-0.7	Vdc
Base – Emitter On Voltage (I _C = -1000 mAdc, V _{CE} = -1.0 Vdc)		V _{BE(on)}	-	-1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				•	
Current–Gain – Bandwidth Product ($I_C = -50$ mAdc, $V_{CE} = -10$ Vdc, $f = 20$ MHz)		f _T	50	_	MHz
Output Capacitance (V _{CB} = -10 Vdc, I _E = 0, f = 1.0 MHz)		C _{obo}	-	30	pF

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

ORDERING INFORMATION

Device	Package	Shipping [†]
MPSW51G	TO-92 (Pb-Free)	5000 Units / Bulk
MPSW51AG	TO-92 (Pb-Free)	5000 Units / Bulk
MPSW51RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
MPSW51ARLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
MPSW51ARLRPG	TO-92 (Pb-Free)	2000 / Ammo Pack

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

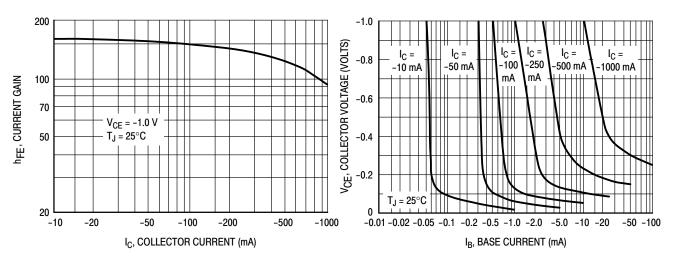


Figure 1. DC Current Gain

Figure 2. Collector Saturation Region

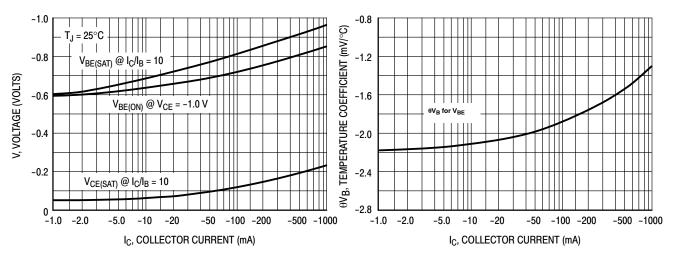


Figure 3. "ON" Voltages

Figure 4. Temperature Coefficient

TYPICAL CHARACTERISTICS

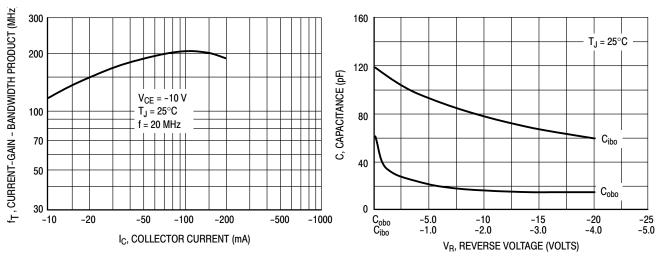


Figure 5. Current Gain — Bandwidth Product

Figure 6. Capacitance

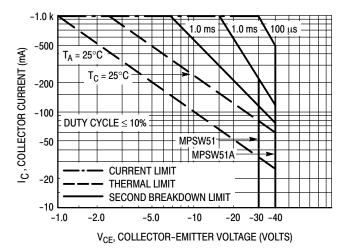
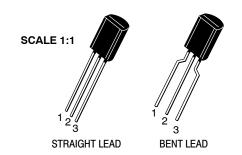


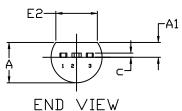
Figure 7. Active Region — Safe Operating Area

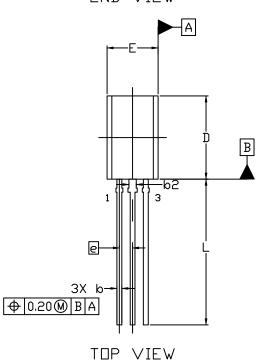


TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE D

DATE 05 MAR 2021

STRAIGHT LEAD





NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION 62 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS						
DIM	MIN.	N□M.	MAX.				
Α	3.75	3.90	4.05				
A1	1.28	1.43	1.58				
b	0.38	0.465	0.55				
b2	0.62	0.70	0.78				
c	0.35	0.40	0.45				
D	7.85	8.00	8.15				
E	4.75	4.90	5.05				
E2	3.90						
е	1.27 BSC						
L	13.80 14.00 14.20						

STYLES AND MARKING ON PAGE 3

DOCUMENT NUMBER:	98AON52857E	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	TO-92 (TO-226) 1 WATT		PAGE 1 OF 3		

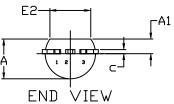
ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

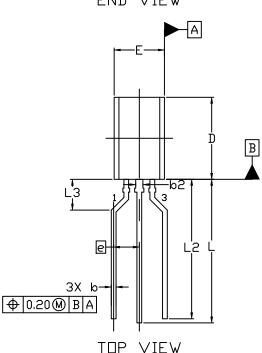


TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE D

DATE 05 MAR 2021

FORMED LEAD





NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION 62 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS						
DIM	MIN.	N□M.	MAX.				
Α	3.75	3.90	4.05				
A1	1.28	1.43	1.58				
Ø	0.38	0.465	0.55				
ь2	0.62	0.70	0.78				
C	0.35	0.40	0.45				
D	7.85	8.00	8.15				
E	4.75	4.90	5.05				
E2	3.90						
е		2.50 BSC					
L	13.80	14.00	14.20				
L2	13.20	13.60	14.00				
L3	3.00 REF						

STYLES AND MARKING ON PAGE 3

DOCUMENT NUMBER:	98AON52857E	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	TO-92 (TO-226) 1 WATT		PAGE 2 OF 3		

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

TO-92 (TO-226) 1 WATT

CASE 29-10 ISSUE D

DATE 05 MAR 2021

STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	PIN 1.	CATHODE CATHODE ANODE		DRAIN SOURCE GATE
	GATE	PIN 1.	SOURCE DRAIN	PIN 1. 2.	DRAIN GATE	STYLE 9: PIN 1. 2. 3.	BASE 1 EMITTER		
2.	CATHODE & ANODE	2.	MAIN TERMINAL 1 GATE MAIN TERMINAL 2	2.	ANODE 1 GATE CATHODE 2	2.	EMITTER		
2.	ANODE	PINI 1	COLLECTOR BASE EMITTER	PIN 1	ANODE	DINI 1		2.	NOT CONNECTED CATHODE ANODE
2.			GATE	PIN 1. 2.	GATE SOURCE DRAIN	PIN 1. 2.	EMITTER COLLECTOR/ANODE CATHODE	PIN 1. 2.	
	V _{CC}		MT SUBSTRATE	PIN 1. 2.	CATHODE	PIN 1. 2.		PIN 1. 2.	
		STYLE 32: PIN 1. 2. 3.	BASE COLLECTOR EMITTER	STYLE 33: PIN 1. 2. 3.	RETURN	PIN 1. 2.	INPUT GROUND LOGIC		

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code

A = Assembly Location

L = Wafer Lot Y = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON52857E	Electronic versions are uncontrolled except when accessed directly from the Document Reposite Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	TO-92 (TO-226) 1 WATT		PAGE 3 OF 3		

ON Semiconductor and III are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability. arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthnoized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800–282–9855 Toll Free USA/Canada

Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

0